NSN 5961-01-344-0958

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-344-0958 **Inclosure Material:** Metal **Mounting Facility Quantity: Component Name And Quantity:** 4 transistor **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** 500.0 drain to source voltage all transistor **Current Rating Per Characteristic:** 164.00 amperes off-state current, peak all transistor and 41.00 amperes drain current all transistor **Power Rating Per Characteristic:** 400.0 watts total device dissipation all transistor **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Terminal Type And Quantity:** 8 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No